

## **New Beam Test Results of 3D Pixel Detectors Constructed With Poly-Crystalline CVD Diamond**

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Toronto, ON, Canada

**Michael Reichmann on behalf of the RD42 Collaboration**

8 August 2019

- 1 Motivation
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- 3 Results
- 4 Conclusion
- 5 Outlook

## Section 1

### Motivation

# Diamond as Detector Material

- innermost tracking layers  $\rightarrow$  highest radiation damage  $\mathcal{O}$  (GHz/cm<sup>2</sup>)
- current detectors would survive  $\sim 12$  month in High-Luminosity LHC
- $\rightarrow$  **R&D for more radiation tolerant detector designs and/or materials**

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## Diamond as Detector Material:

- properties
  - ▶ radiation tolerant
  - ▶ isolating material
  - ▶ high charge carrier mobility
  - ▶ smaller signal than in silicon with same thickness (large bandgap)
  - ▶ after  $1 \cdot 10^{16}$  n/cm<sup>2</sup> the mean drift path in diamond larger than in silicon

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## Work of RD42:

- investigate signals and radiation tolerance in various detector designs:
  - ▶ Pad Detectors  $\rightarrow$  whole diamond as single cell readout (Lukas' Talk)
  - ▶ Pixel Detectors  $\rightarrow$  diamond sensor on pixel readout chip
  - ▶ 3D Pixel Detectors  $\rightarrow$  3D diamond detector on pixel readout chip

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  - ▶ Pad Detectors
  - ▶ Pixel Detectors
  - ▶ 3D Pixel Detectors  $\rightarrow$  this talk

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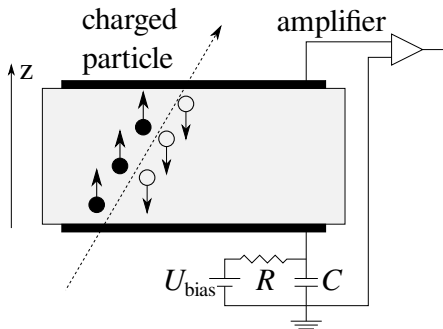
30 institutes



## Section 2

### 3D Diamond Detector

# Diamond as Particle Detector



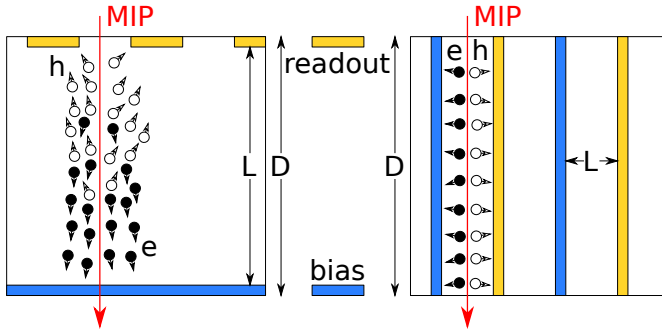
(a) Detector Schematics



(b) 15 cm  $\varnothing$  pCVD Diamond Wafer

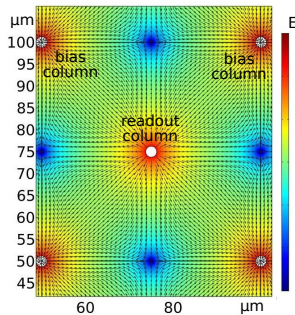
- detectors function as ionisation chambers
- metallisation on both sides
- poly-crystals produced in large wafers

# Working Principle



- after large radiation fluence all detectors become trap limited
- 3D = bias and readout electrode inside detector material
- same thickness  $D \rightarrow$  same amount of induced charge  $\rightarrow$  shorter drift distance  $L$
- **increase collected charge in detectors with limited mean drift path (Schubweg)**
- **introduce low field regions**

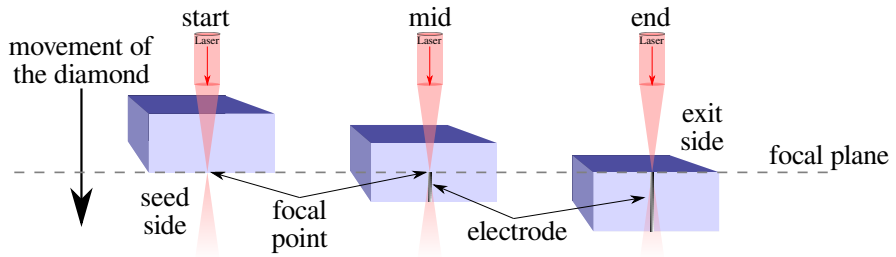
# Electric Field Simulation



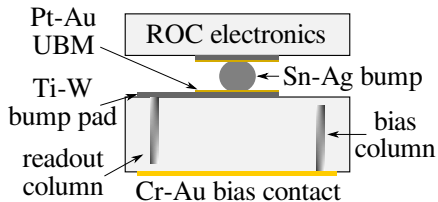
- simulation with 30 V bias voltage and periodic boundary conditions
- electric field  $\sim 1 \text{ V}/\mu\text{m}$  over a large area in the cell
- low field region in between the electrodes

# Laser drilling

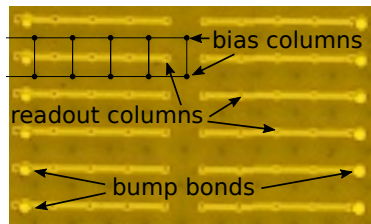
- “drilling” columns using 800 nm fs-LASER (Oxford)
- convert diamond into resistive mixture of carbon phases (i.a. DLC, graphite, ...)
- usage of Spatial Light Modulator (SLM) to correct for spherical aberration
- initial column yield  $\sim 90\%$   $\rightarrow$  now  $\gtrsim 99.8\%$
- initial column diameter  $6 \sim 10\ \mu\text{m}$   $\rightarrow$  now  $2.6\ \mu\text{m}$



# Bump Bonding



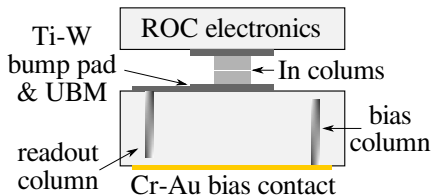
(a) Bump bond schematics



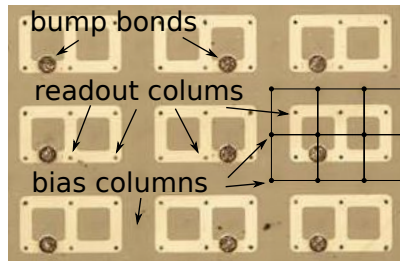
(b)  $5 \times 1$  bump pads

- connection to bias and readout with surface metallisation
- ganging of cells to match pixel pitch of readout-chip (ROC)
- small gap ( $\sim 15 \mu\text{m}$ ) to the surface

# Bump Bonding



(a) Bump bond schematics



(b)  $3 \times 2$  bump pads

- connection to bias and readout with surface metallisation
- ganging of cells to match pixel pitch of readout-chip (ROC)
- small gap ( $\sim 15 \mu\text{m}$ ) to the surface

# Progress in Diamond Detectors

## 3D Detectors - History in Diamonds:

- proved that 3D works in pCVD diamond
- scale up the number of 3D-cells per detector:  $\mathcal{O}(100) \rightarrow \mathcal{O}(4000) (\times 40)$
- reducing the cell size:  $150\text{ }\mu\text{m} \times 150\text{ }\mu\text{m} \rightarrow 50\text{ }\mu\text{m} \times 50\text{ }\mu\text{m} \rightarrow 25\text{ }\mu\text{m} \times 25\text{ }\mu\text{m}$  (soon)
- reducing the diameter of the columns:  $6 \sim 10\text{ }\mu\text{m} \rightarrow 2.6\text{ }\mu\text{m} \rightarrow 1 \sim 2\text{ }\mu\text{m}$  (soon)
- $\rightarrow$  increasing column yield:  $\sim 90\% \rightarrow \gtrsim 99.8\%$
- recent beam test of irradiated  $50\text{ }\mu\text{m} \times 50\text{ }\mu\text{m}$  3D detector ( $3.5 \cdot 10^{15}\text{ n/cm}^2$ )

## 3D Pixel Detectors:

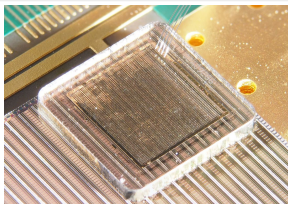
- visible improvements with each step reducing the cell size
- all worked as expected (to first order)



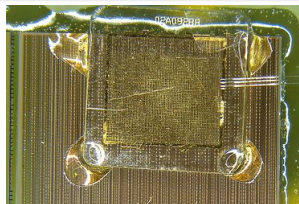
## Section 3

### Results

## Detectors



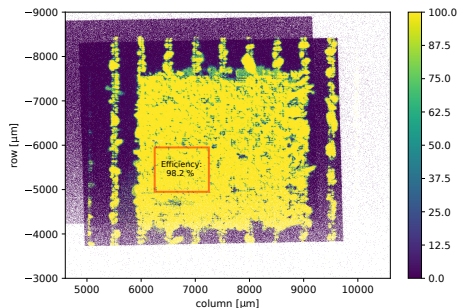
(a) B5



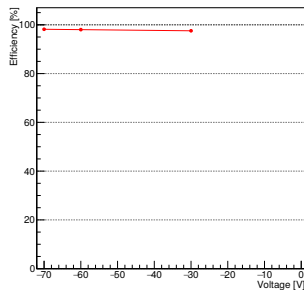
(b) B6

	B5	B6
readout chip (ROC)	FE-I4B	PSI46digv2.1respin
pixel pitch	$250\ \mu\text{m} \times 50\ \mu\text{m}$	$150\ \mu\text{m} \times 100\ \mu\text{m}$
3D cell size	$50\ \mu\text{m} \times 50\ \mu\text{m}$	$50\ \mu\text{m} \times 50\ \mu\text{m}$
ganging	$5 \times 1$	$3 \times 2$
size	$4.90\ \text{mm} \times 4.94\ \text{mm}$	$4.85\ \text{mm} \times 4.90\ \text{mm}$
thickness	$510\ \mu\text{m}$	$500\ \mu\text{m}$
50 pixels $\times$ 50 pixels	$53 \times 67$	$67 \times 53$
3D columns	7223	7223
column diameter	$2.6\ \mu\text{m}$	$2.6\ \mu\text{m}$
active area	$3.2\ \text{mm} \times 3.5\ \text{mm}$	$3.45\ \text{mm} \times 3.19\ \text{mm}$
bump bonding	tin silver (IFAE)	indium (Princeton)

# B5 (5 × 1) - Efficiency @ CERN



(a) Efficiency map @ -70 V



(b) Efficiency vs. bias voltage.

- telescope tracking resolution at DUT:  $\sim 3 \mu\text{m}$
- threshold of the chip:  $\sim 1000 e$
- efficiency in red fiducial area 98.2 %
- inefficiencies most likely due to processing issues

# Time Over Threshold

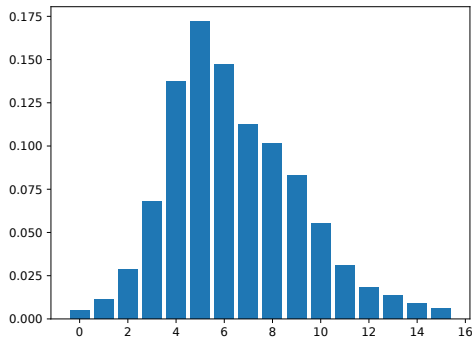
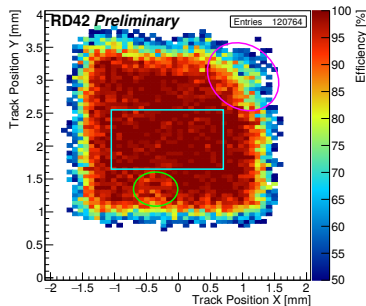


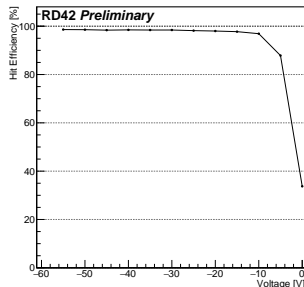
Figure: Time over threshold distribution.

- looks very similar to silicon distribution
- $5 \text{ tot} \approx 11\,000 \text{ e}$
- mean of the ToT distribution:  $6.7 \rightarrow \sim 14\,500 \text{ e}$
- $\sim 80\%$  the induced charge was collected

## B6 (3 × 2) - Efficiencies @ PSI



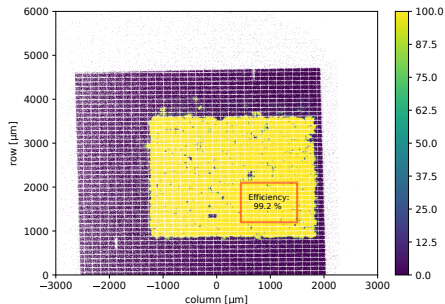
(a) Efficiency Map



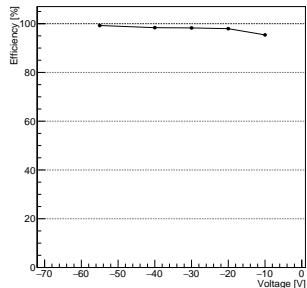
(b) Efficiency vs. voltage.

- telescope tracking resolution at DUT:  $\varnothing$  (100  $\mu$ m)
- magenta area  $\rightarrow$  bump bonding problems, green area  $\rightarrow$  void in the diamond
- efficiency in blue box: 99.2 % ( $\rightarrow$  99.6 % expected due to columns)
- efficiency already plateaus at 30 V
- ROC stopped working after this beam test

# Efficiencies @ CERN



(a) Efficiency at threshold of  $\sim 3500$  e.



(b) Efficiency vs. bias voltage.

- high resolution measurement at CERN
- locate non-working/non-connected cells
- sensor twice re-bump-bonded with the same indium (no reprocessing)
  - ▶ no removal of old bumps, no change of surface metallisation
- same efficiency: 99.2 %

# Pulse Height @ CERN

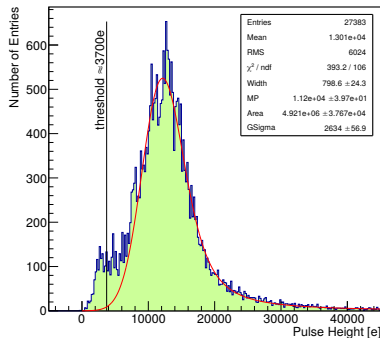


Figure: Pulse height distribution.

- threshold of the chip:  $\sim 3700$  e
- mean from MC of Langau fit:  $\sim 14500$  e
- pulse height very similar to  $5 \times 1$  result at CERN
- distribution below threshold not understood (maybe local data transmission issues)

## Section 4

### Conclusion



# Conclusion

- 3D Detectors work well in pCVD diamond
- strongly improved fabrication of 3D diamond detectors
  - ▶  $40 \times$  more cells
  - ▶ smaller cell size down to  $50 \mu\text{m} \times 50 \mu\text{m}$
  - ▶ thinner columns down to  $2.6 \mu\text{m}$
- general reasons for inefficiencies:
  - ▶ less charge created in the volume of the electrodes (0.4 % for shown devices)
  - ▶ missing/broken columns (0.2 % for the full device)
  - ▶ region with low electric field  $\rightarrow$  need precise simulations
- $(99.2 \pm 0.3) \%$  efficiency in  $3 \times 2$  ganged device
- $(98.2 \pm 0.2) \%$  efficiency in  $5 \times 1$  ganged device
  - ▶ discrepancy most likely due to different processing and bump bonding
- consistent mean charge measurements for all devices:  $\sim 14\,500\text{ e}$  @ CERN SPS
  - ▶ working on systematic effects
- 3D has largest charge collection of all pCVD diamond detectors
  - ▶ work towards quantifying the charge collection in both non- and irradiated devices

## Section 5

### Outlook

# Outlook

- analyse  $3.5 \cdot 10^{15} \text{ n/cm}^2$  irradiated  $50 \mu\text{m} \times 50 \mu\text{m}$  detectors
- test both  $50 \mu\text{m} \times 50 \mu\text{m}$  and  $25 \mu\text{m} \times 25 \mu\text{m}$  pixel detectors
- reduce column diameter to  $1 \sim 2 \mu\text{m}$
- build pixel device on newest RD53 chip ( $50 \mu\text{m} \times 50 \mu\text{m}$  pixel pitch)
- continue scale up by  $10 \times$

# DEL FIN

